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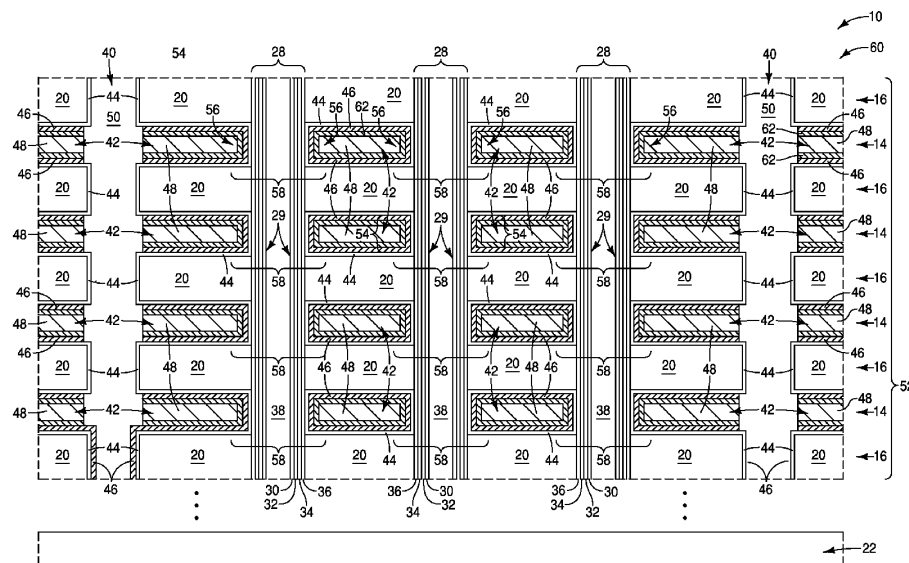


FIG. 20

(57) Abstract: Some embodiments include a memory cell having a conductive gate comprising ruthenium. A charge-blocking region is adjacent the conductive gate, a charge-storage region is adjacent the charge-blocking region, a tunneling material is adjacent the charge-storage region, and a channel material is adjacent the tunneling material. Some embodiments include an assembly having a vertical stack of alternating insulative levels and wordline levels. The wordline levels contain conductive wordline material which includes ruthenium. Semiconductor material extends through the stack as a channel structure. Charge-storage regions are between the conductive wordline material and the channel structure. Charge-blocking regions are between the charge-storage regions and the conductive wordline material. Some embodiments include methods of forming integrated assemblies.

[Continued on next page]

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